DATARAM
Accelerating Innovation

DVM26S1T8/8G
8GB - 260-Pin 1Rx8 Unbuffered Non-ECC DDR4 SODIMM

Identification
DVM26S1T8/8G 1Gx64
8GB 1Rx8 PC4-2666V-S19

Performance Range
Clock / Module Speed / CL-t_{RCD} –t_{RP}
1333MHz / PC4-2666 / 19-19-19
1200 MHz / PC4-2400 / 17-17-17
1067MHz / PC4-2133 / 15-15-15
933 Hz / PC4-1866 / 13-13-13
800 Hz / PC4-1600 / 11-11-11

Features

260-pin JEDEC-compliant DIMM, 69.60 mm wide by 30.00 mm high
Operating Voltage: VDD/VDDQ = 1.2V (1.14V to 1.26V)
Operating Temperature (Environment, Ambient T_{OPR}) – 0 to 65 C
Operating Temperature (DRAM T_{OPER}) – 0 to 85 C
VPP = 2.5V (2.375V to 2.75V)
VDDSPD = 2.25V to 2.75V
I/O Type: 1.2 V signaling
On-board I^{2}C Serial Presence-Detect (SPD) EEPROM
Data Transfer Rate: 21.3 Gigabytes/sec
Data Bursts: 8 and burst chop 4 mode
ZQ Calibration for Output Driver and On-Die Termination (ODT)
Programmable ODT / Dynamic ODT during Writes
Programmable CAS Latency: 10, 11, 12, 13, 14, 15, 16, 17, 18 and 19
Bi-directional Differential Data Strobe signals
Per DRAM Addressability is supported
Write CRC is supported at all speed grades
DBI (Data Bus Inversion) is supported(x8 only)
CA parity (Command/Address Parity) mode is supported
16 internal banks
SDRAM Addressing (Row/Col/BG/BA): 16/10/2/2
Fully RoHS Compliant

Description

DVM26S1T8/8G is an Unbuffered 1Gx64 small – outline memory module, which conforms to JEDEC's DDR4-2666, PC4-2666 standard. The assembly is Single-Rank, comprised of eight 1Gbx8 DDR4-2666 SDRAMs.
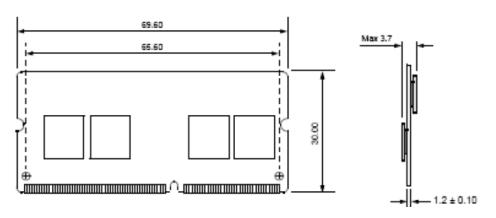
One EEPROM is used for Serial Presence Detect.

Both output driver strength and input termination impedance are programmable to maintain signal integrity on the I/O signals in a Fly-by topology.

Notes

Tolerances on all dimensions except where otherwise indicated are ±.13 (.005).
All dimensions are expressed in millimeters [inches]

Units : Millimeters